METHOD OF PROCESSING SUBSTRATE, METHOD OF MANUFACTURING SEMICONDUCTOR DEVICE, PROGRAM, AND SUBSTRATE PROCESSING APPARATUS

ABSTRACT

There is provided a technique that includes: (a) arranging a plurality of first substrates, each including a surface on which a concave structure is formed, in multiple stages within a first region along a direction perpendicular to the surface; (b) supplying a first processing gas toward at least a portion of the first region; and (c) supplying an inert gas different from the first processing gas toward the at least a portion of the first region, wherein the first region includes a first zone including one end of the first region, a third zone including the other end of the first region, and a second zone located between the first zone and the third zone.

Fig. 4